

Power MOSFETs

Q-Class

IXTQ 23N60Q

$$V_{DSS} = 600 \text{ V}$$

$$I_{D25} = 23 \text{ A}$$

$$R_{DS(on)} = 0.32 \text{ } \Omega$$

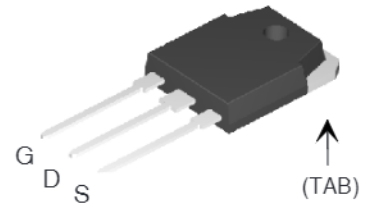
N-Channel Enhancement Mode
 Avalanche Rated, High dv/dt,
 Low Gate Charge and Capacitances

Preliminary Data Sheet



Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	$T_J = 25^\circ\text{C to } 150^\circ\text{C}$	600	V
V_{DGR}	$T_J = 25^\circ\text{C to } 150^\circ\text{C}; R_{GS} = 1 \text{ M}\Omega$	600	V
V_{GS}	Continuous	± 30	V
V_{GSM}	Transient	± 40	V
I_{D25}	$T_C = 25^\circ\text{C}$	23	A
I_{DM}	$T_C = 25^\circ\text{C}$, pulse width limited by T_{JM}	92	A
I_{AR}	$T_C = 25^\circ\text{C}$	23	A
E_{AR}	$T_C = 25^\circ\text{C}$	30	mJ
E_{AS}	$T_C = 25^\circ\text{C}$	1.5	J
dv/dt	$I_S \leq I_{DM}$, $di/dt \leq 100 \text{ A}/\mu\text{s}$, $V_{DD} \leq V_{DSS}$, $T_J \leq 150^\circ\text{C}$, $R_G = 2 \text{ } \Omega$	5	V/ns
P_D	$T_C = 25^\circ\text{C}$	400	W
T_J		-55 ... +150	$^\circ\text{C}$
T_{JM}		150	$^\circ\text{C}$
T_{stg}		-55 ... +150	$^\circ\text{C}$
T_L	1.6 mm (0.062 in.) from case for 10 s	300	$^\circ\text{C}$
M_d	Mounting torque	1.13/10	Nm/lb.in.
Weight		6	g

TO-3P (IXTQ)



G = Gate D = Drain
 S = Source TAB = Drain

Features

- IXYS advanced low gate charge process
- International standard package
- Low gate charge and capacitance
 - easier to drive
 - faster switching
- Low $R_{DS(on)}$
- Unclamped Inductive Switching (UIS) rated
- Molding epoxies meet UL 94 V-0 flammability classification

Advantages

- Easy to mount
- Space savings
- High power density

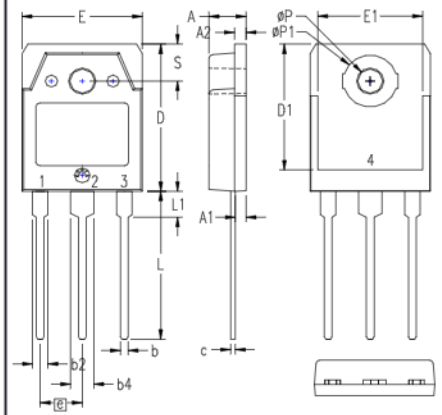
Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
V_{DSS}	$V_{GS} = 0 \text{ V}$, $I_D = 250 \text{ } \mu\text{A}$	600		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250 \text{ } \mu\text{A}$	2.5		4.5 V
I_{GSS}	$V_{GS} = \pm 30 \text{ V}_{DC}$, $V_{DS} = 0$			$\pm 100 \text{ nA}$
I_{DSS}	$V_{DS} = V_{DSS}$, $T_J = 25^\circ\text{C}$			25 μA
	$V_{GS} = 0 \text{ V}$, $T_J = 125^\circ\text{C}$			1 mA
$R_{DS(on)}$	$V_{GS} = 10 \text{ V}$, $I_D = 0.5 I_{D25}$ Pulse test, $t \leq 300 \text{ } \mu\text{s}$, duty cycle $d \leq 2 \%$			0.32 Ω

Symbol	Test Conditions	Characteristic Values		
		(T _J = 25°C, unless otherwise specified)		
		Min.	Typ.	Max.
g_{fs}	V _{DS} = 10 V; I _D = 0.5 I _{D25} , pulse test	10	20	S
C_{iss}	V _{GS} = 0 V, V _{DS} = 25 V, f = 1 MHz		3300	pF
C_{oss}			410	pF
C_{rss}			130	pF
t_{d(on)}	V _{GS} = 10 V, V _{DS} = 0.5 V _{DSS} , I _D = 0.5 I _{D25} R _G = 1.5 Ω (External)		20	ns
t_r			20	ns
t_{d(off)}			45	ns
t_f			20	ns
Q_{g(on)}	V _{GS} = 10 V, V _{DS} = 0.5 V _{DSS} , I _D = 0.5 I _{D25}		90	nC
Q_{gs}			20	nC
Q_{gd}			45	nC
R_{thJC}			0.31	K/W
R_{thCK}			0.25	K/W

Source-Drain Diode

Symbol	Test Conditions	Characteristic Values		
		(T _J = 25°C, unless otherwise specified)		
		min.	typ.	max.
I_S	V _{GS} = 0 V			23 A
I_{SM}	Repetitive; pulse width limited by T _{JM}			92 A
V_{SD}	I _F = I _S , V _{GS} = 0 V, Pulse test, t ≤ 300 μs, duty cycle d ≤ 2 %			1.5 V
t_{rr}	I _F = I _S , -di/dt = 100 A/μs, V _R = 100 V		500	ns

TO-3P Outline



SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.185	.193	4.70	4.90
A1	.051	.059	1.30	1.50
A2	.057	.065	1.45	1.65
b	.035	.045	0.90	1.15
b2	.075	.087	1.90	2.20
b4	.114	.126	2.90	3.20
c	.022	.031	0.55	0.80
D	.780	.791	19.80	20.10
D1	.665	.677	16.90	17.20
E	.610	.622	15.50	15.80
E1	.531	.539	13.50	13.70
e	.215 BSC		5.45 BSC	
L	.779	.795	19.80	20.20
L1	.134	.142	3.40	3.60
φP	.126	.134	3.20	3.40
φP1	.272	.280	6.90	7.10
S	.193	.201	4.90	5.10

All metal area are tin plated.

- 1 - GATE
- 2 - DRAIN (COLLECTOR)
- 3 - SOURCE (EMITTER)
- 4 - DRAIN (COLLECTOR)

Fig. 1. Output Characteristics @ 25 Deg. C

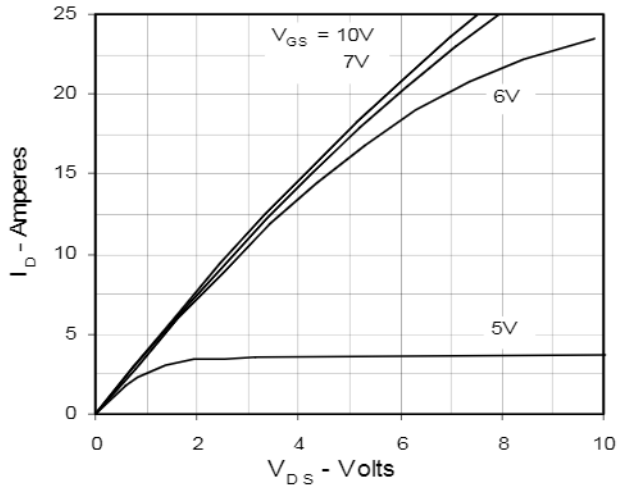


Fig. 2. Extended Output Characteristics @ 25 deg. C

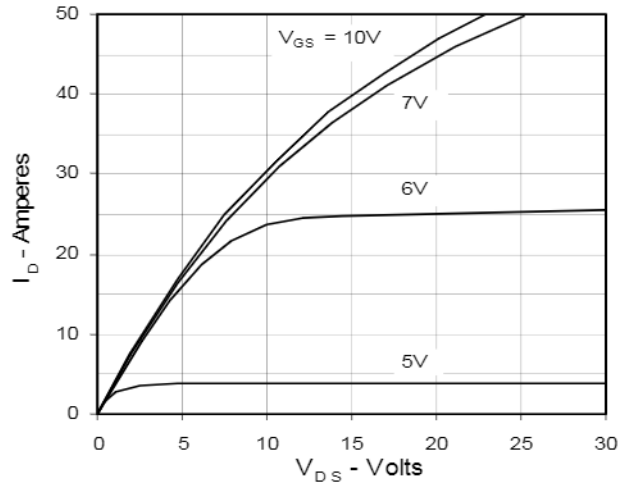


Fig. 3. Output Characteristics @ 125 Deg. C

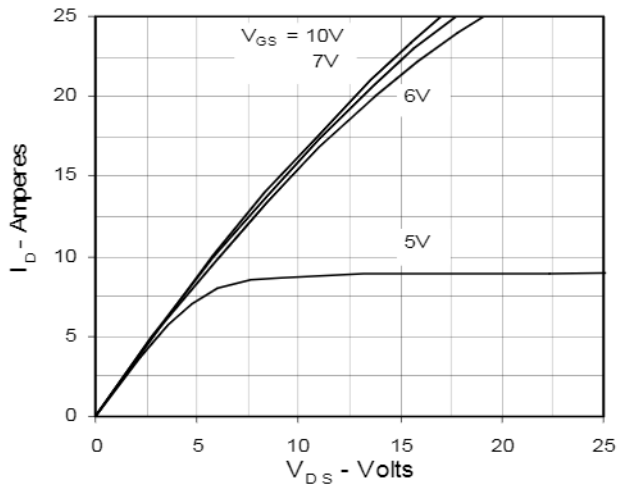


Fig. 4. R_DS(on) Normalized to I_D25 Value vs. Junction Temperature

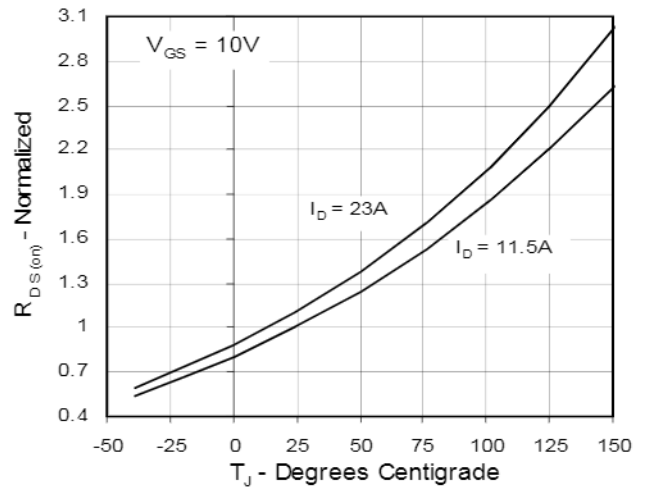


Fig. 5. R_DS(on) Normalized to I_D25 Value vs. I_D

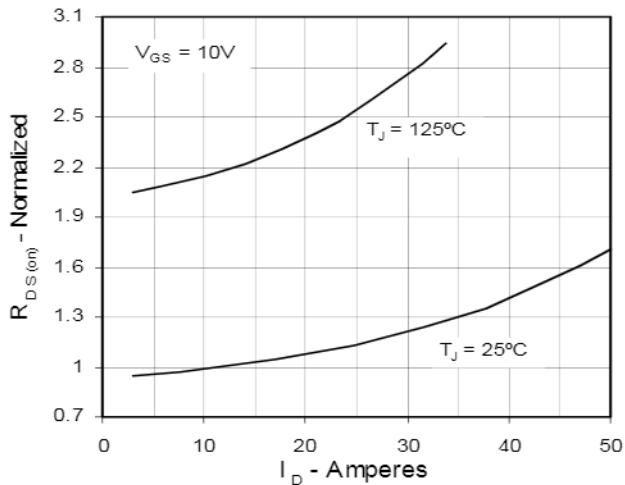


Fig. 6. Drain Current vs. Case Temperature

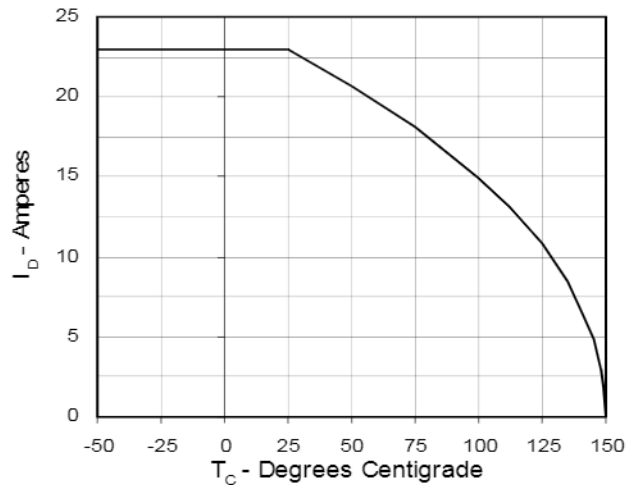


Fig. 7. Input Admittance

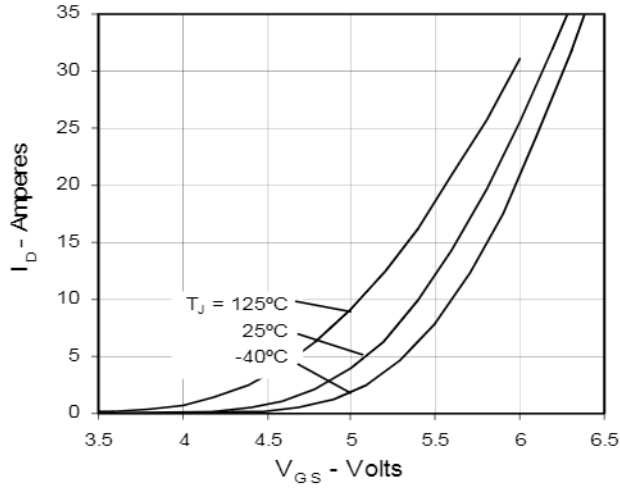


Fig. 8. Transconductance

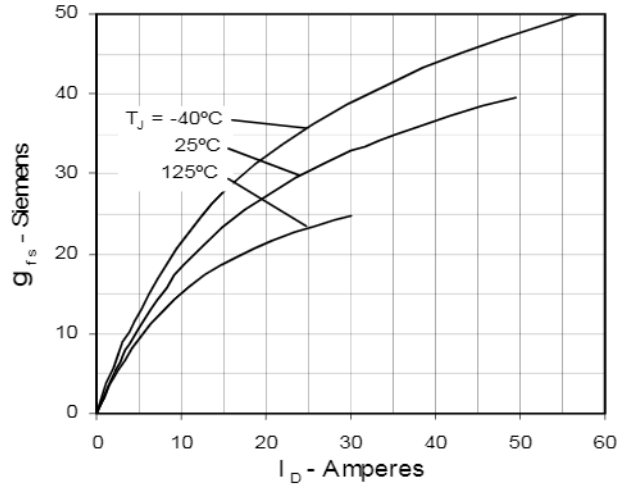


Fig. 9. Source Current vs. Source-To-Drain Voltage

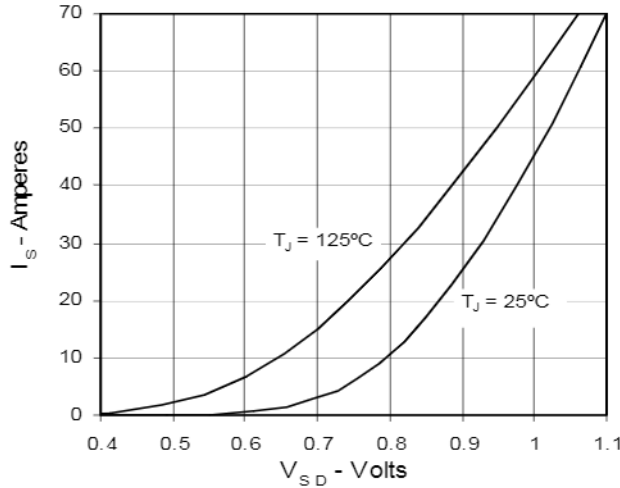


Fig. 10. Gate Charge

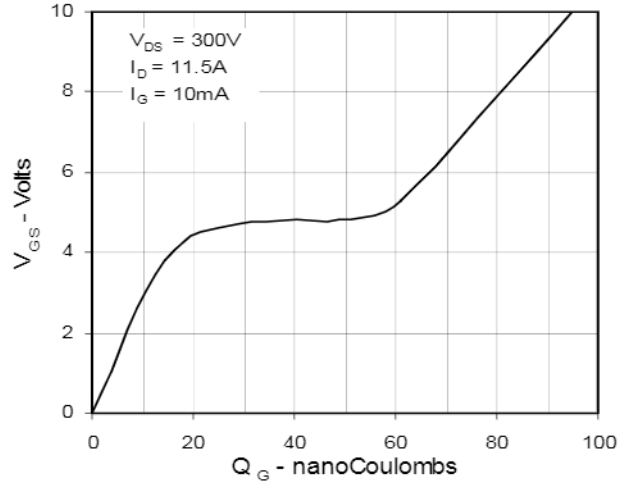


Fig. 11. Capacitance

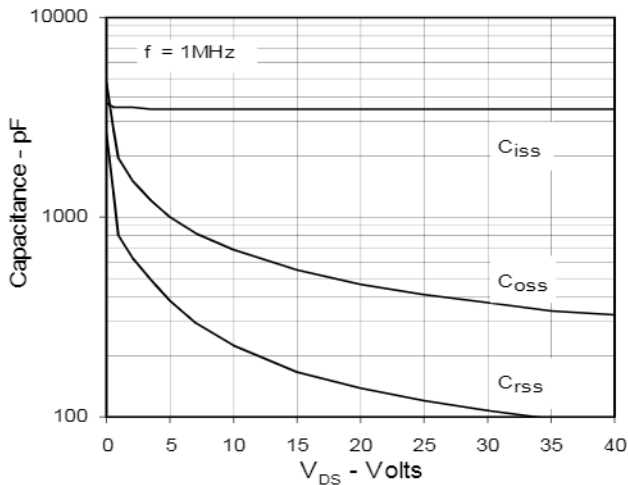
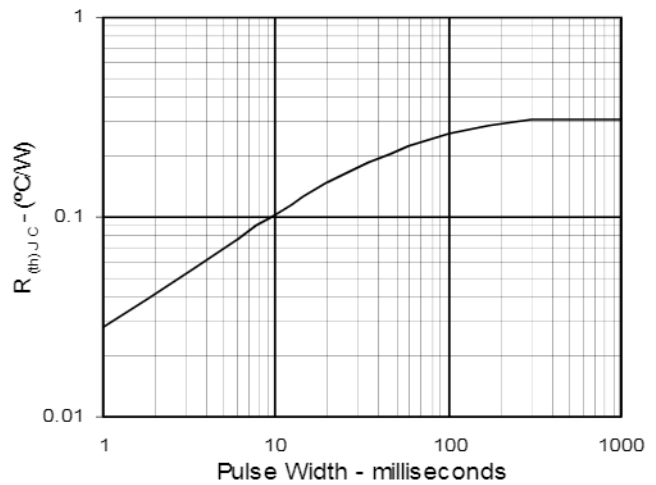


Fig. 12. Maximum Transient Thermal Resistance



IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:

4,835,592 4,881,106 5,017,508 5,049,961 5,187,117 5,486,715 6,306,728B1 6,259,123B1 6,306,728B1
4,850,072 4,931,844 5,034,796 5,063,307 5,237,481 5,381,025 6,404,065B1 6,162,665 6,534,343